HIGH-SPEED 3.3V 64K x 18 SYNCHRONOUS PIPELINED DUAL-PORT STATIC RAM WITH 3.3V OR 2.5V INTERFACE

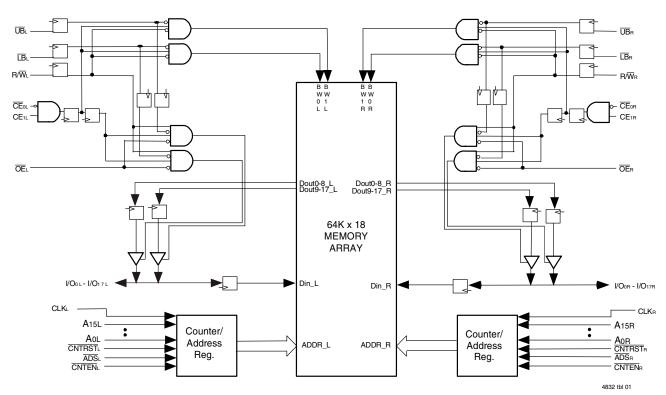
Features

- True Dual-Port memory cells which allow simultaneous access of the same memory location
- High-speed clock to data access
 - Commercial: 4.2/5/6ns (max.)
 - Industrial: 5ns (max)
- Pipelined output mode
- Counter enable and reset features
- Dual chip enables allow for depth expansion without additional logic
- Full synchronous operation on both ports
 - 7.5ns cycle time, 133MHz operation (9.6 Gbps bandwidth)
 - Fast 4.2ns clock to data out
 - 1.8ns setup to clock and 0.7ns hold on all control, data, and address inputs @ 133MHz

- Data input, address, byte enable and control registers

70V3389S

- Self-timed write allows fast cycle time
- Separate byte controls for multiplexed bus and bus matching compatibility
- LVTTL- compatible, single 3.3V (±150mV) power supply for core
- LVTTL- compatible, selectable 3.3V (±150mV)/2.5V (±125mV) power supply for I/Os and control signals on each port
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Available in a 128-pin Thin Quad Plastic Flatpack (TQFP), 208-pin fine pitch Ball Grid Array, and 256-pin Ball
- Grid Array
 Green parts available, see ordering information



Functional Block Diagram

70V3389S High-Speed 64K x 18 3.3V Dual-Port Synchronous Pipelined Static RAM

Description:

The IDT70V3389 is a high-speed 64K x 18 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times. With an input data register, the IDT70V3389 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by \overline{CE}_0 and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode.

The 70V3389 can support an operating voltage of either 3.3V or 2.5V on one or both ports, controllable by the OPT pins. The power supply for the core of the device (VDD) remains at 3.3V.

1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	_
I/O9L	NC	Vss	NC	NC	NC	A12L	A8L	NC	Vdd	CLK∟	CNTEN L	A4L	Aol	OPT∟	NC	Vss	A
NC	Vss	NC	Vss	NC	A13L	A9L	NC		Vss	ADSL	A5L	Aıl	Vss	VDDQR	I/O8L	NC	В
VDDQL	I/O9r	VDDQR	Vdd	NC	A14L	A10L	Ū₿∟	CE1L	Vss	R/₩L	A6L	A2L	Vdd	I/O8r	NC	Vss	С
NC	Vss	I/O10L	NC	A15L	A11L	A7L	<u>LB</u> L	Vdd	ŌĒL	ONTRST I	A3L	Vdd	NC	Vddql	I/O7L	I/O7r	D
I/O11L	NC	Vddqr	I/O10R		-									NC	Vss	NC	E
VDDQL	I/O11R	NC	Vss											I/O6r	NC	Vddqr	F
NC	Vss	I/O12L	NC											Vddql	I/O5l	NC	G
Vdd	NC	Vddqr	I/O12R)V33					Vdd	NC	Vss	I/O5r	н
Vddql	Vdd	Vss	Vss				В	F208	(5)				Vss	VDD	Vss	Vddqr	J
I/O14R	Vss	I/O13R	Vss					08-Pi pBG/					I/O3r	VDDQL	I/O4r	Vss	ĸ
NC	I/O14L	Vddqr	I/O13L				Тор	o Vie	W ⁽⁶⁾				NC	I/O3L	Vss	I/O4L	L
VDDQL	NC	I/O15R	Vss										Vss	NC	I/O2r	VDDQR	М
NC	Vss	NC	I/O15L										I/O1r	VDDQL	NC	I/O2L	N
I/O _{16R}	I/O16L	Vddqr	NC	NC	NC	A12R	Aar	NC	Vdd	CLKR	ONTEN R	A4R	NC	I/O1L	Vss	NC	P
Vss	NC	I/O17R	NC	NC	A13R	A9R	NC	CEOR	Vss	ADSR	A5R	A1R	Vss	VDDQL	I/Oor	Vddqr	R
NC	I/O17L	Vddql	Vss	NC	A14R	A10R	UBR	CE1R	Vss	R/WR	A6R	A2R	Vss	NC	Vss	NC	Т
Vss	NC	Vdd	NC	A15R	A11R	A7R	LBR	Vdd	ŌĒr	ONTRST F	Азв	AOR	Vdd	OPTR	NC	I/Ool	U
		•											•			4832 tb	102

Pin Configuration^(1,2,3,4)

- 1. All VDD pins must be connected to 3.3V power supply.
- 2. All VDDO pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).
- 3. All Vss pins must be connected to ground supply.
- 4. Package body is approximately 15mm x 15mm x 1.4mm with 0.8mm ball pitch.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

70V3389S High-Speed 64K x 18 3.3V Dual-Port Synchronous Pipelined Static RAM

4832 drw 02c

Pin Configuration^(1,2,3,4) (con't.)

70V3389 BC256⁽⁵⁾ BCG256⁽⁵⁾

256-Pin BGA Top View⁽⁶⁾

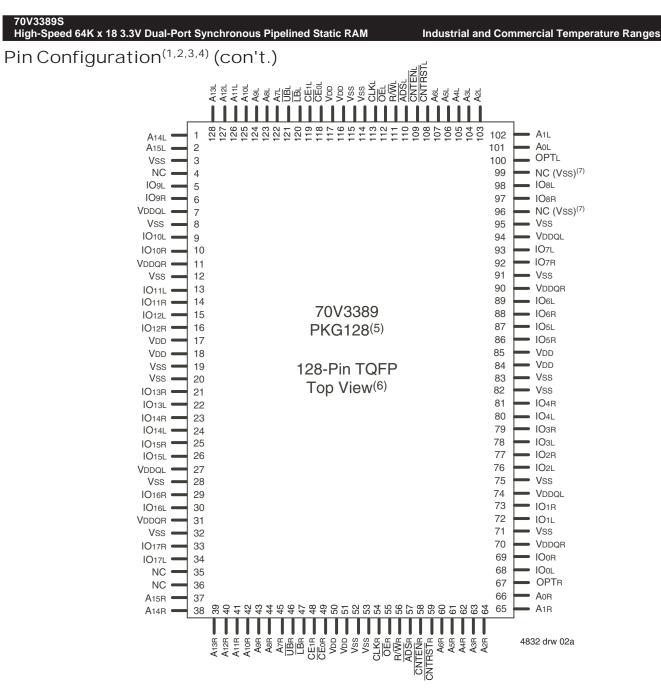
							ισρ	VICVV							
A1	A2	A3	A4	A5	A6	A7	A8	A9	A10	A11	A12	A13	A14	A15	A16
NC	NC	NC	NC	A14L	A11L	A8L	NC	CE1L	OEL	CNTENL	A 5L	A2L	A0L	NC	NC
^{B1}	^{B2}	^{B3} NC	^{B4}	B5	B6	B7	b8	B9	B10	B 1 1	B12	B13	B14	B15	^{B16}
NC	NC		NC	A15L	A12L	A9L	UBl	CE0L	R/WL	CNTRSTL	A4L	A1L	Vdd	NC	NC
C1	C2	C3	C4	C5	C6	C7	C8	C9	C10	C11	C12	C13	C14	C15	C16
NC	I/O9L	Vss	NC	A13L	A10L	A7L	NC	LBL	CLKL	ADSL	A6L	A3L	OPT∟	NC	I/O8L
D1	d2	D3	d4	d5	d6	d7	d8	d9	d10	d11	d12	D13	D14	D15	d16
NC	I/O9r	NC	Vdd	Vddql	Vddql	Vddqr	Vddqr	Vddql	Vddql	Vddqr	Vddqr	Vdd	NC	NC	I/O8r
e1		E3	e4	e5	e6	e7	^{E8}	^{E9}	E10	e11	e12	e13	E14	e15	e16
I/O10r		NC	Vddql	Vdd	Vdd	Vss	Vss	Vss	Vss	Vdd	Vdd	Vddqr	NC	I/O7l	I/O7r
F1	F2	f3	f4	f5	F6	F7	F8	^{F9}	F10	F11	F12	f13	f14	F15	F16
I/O11L	NC	I/O11r	Vddql	Vdd	Vss	Vss	Vss	Vss	Vss	Vss	Vdd	Vddqr	I/O6r	NC	I/O6l
G1	G2	g3	g4	_{G5}	_{G6}	_{G7}	G8	^{G9}	G10	G11	G12	g13	g14	G15	G16
NC	NC	I/O12L	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddql	I/O5l	NC	NC
H1	h2	H3	h4	^{H5}	H6	^{H7}	H8	H9	H10	H11	H12	h13	H14	H15	h16
NC	I/O12R	NC	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddql	NC	NC	I/O5r
J1	J2	j3	j4	_{J5}	_{J6}	J7	_{J8}	^{J9}	J10	J11	J12	j13	J14	j15	J16
I/O13L	I/O14R	I/O13R	Vddql	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	I/O4r	I/O3r	I/O4L
K1	K2	k3	k4	^{K5}	K6	к7	ка	к9	K10	K11	K12	k13	K14	K15	к16
NC	NC	I/O14L	Vddql	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	NC	NC	I/Oзl
l1	L2	l3	l4	l5	L6	L7	L8	L9	L10	L11	l12	l13	l14	L15	l16
I/O15L	NC	I/O15R	Vddqr	Vdd	Vss	Vss	Vss	Vss	Vss	Vss	Vdd	Vddql	I/O2l	NC	I/O2R
м1	m2	^{мз}	m4	^{M5}	M6	M7	^{M8}	M9	M10	M11	M12	m13	^{M14}	^{M15}	M16
I/O16R	I/O16L	NC	Vddqr	Vdd	Vdd	Vss	Vss	Vss	Vss	Vdd	Vdd	Vddql	I/O1r	I/O1L	NC
N1	n2	N3	N4	n5	n6	n7	n8	n9	n10	n11	n12	N13	N14	n15	N16
NC	I/O17r	NC	Vdd	Vddqr	Vddqr	Vddql	Vddql	Vddqr	Vddqr	Vddql	Vddql	Vdd	NC	I/Oor	NC
P1	p2	P3	P4	P5	P6	P7	P8	P9	P10	^{P11}	P12	P13	P14	P15	p16
NC	I/O17L	NC	NC	A13R	A10R	A7R	NC	LBr	CLKR	ADSr	A 6R	A3R	NC	NC	I/Ool
^{R1}	^{R2}	^{R3}	^{R4}	R5	R6	R7	r8	R9	r10	^{r11}	R12	R13	^{R14}	^{R15}	R16
NC	NC	NC	NC	A15R	A12R	A 9R	UBr	CE0R	R/Wr	CNTRSTr	A 4R	A 1R	OPTr	NC	NC
T1	T2	тз	T4	T5	т6	t7	T8	^{T9}	T10	t11	T12	T13	T14	T15	^{T16}
NC	NC	NC	NC	A 14R	А 11R	A8r	NC	CE1R	OEr	CNTENR	A 5R	A 2R	Aor	NC	NC
												-			

NOTES:

1. All VDD pins must be connected to 3.3V power supply.

2. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIH (0.1).

- 3. All Vss pins must be connected to ground supply.
- 4. Package body is approximately 17mm x 17mm x 1.4mm, with 1.0mm ball-pitch.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.



- 1. All VDD pins must be connected to 3.3V power supply.
- 2. All VDDD pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).
- 3. All Vss pins must be connected to ground supply.
- 4. Package body is approximately 14mm x 20mm x 1.4mm.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.
- 7. In the 70V3379 (32K x 18) and 70V3389 (64K x 18), pins 96 and 99 are NC. The upgrade devices 70V3399 (128K x 18) and 70V3319 (256K x 18) assign these pins as Vss. Customers who plan to take advantage of the upgrade path should treat these pins as Vss on the 70V3379 and 70V3389. If no upgrade is needed, the pins can be treated as NC.

70V3389S High-Speed 64K x 18 3.3V Dual-Port Synchronous Pipelined Static RAM

Pin Names

Left Port	Right Port	Names						
CE0L, CE1L	CEOR, CE1R	Chip Enables						
R/WL	R/WR	Read/Write Enable						
OEL OER		Output Enable						
Aol - A15l Aor - A15r		Address						
1/Ool - 1/O17L	1/Oor - 1/017r	Data Input/Output						
CLKL	CLKR	Clock						
ĀDĪSL	ADS R	Address Strobe Enable						
		Counter Enable						
CNTRSTL		Counter Reset						
UBL - LBL	UBr - LBr	Byte Enables (9-bit bytes)						
VDDQL	VDDQR	Power (VO Bus) (3.3V or 2.5V) ⁽¹⁾						
OPTL	OPTR	Option for selecting VDDax ^(1,2)						
	Vdd	Power (3.3V) ⁽¹⁾						
	Vss	Ground (0V)						
4832 tbl 01								

Industrial and Commercial Temperature Ranges

NOTES:

- 1. VDD, OPTx, and VDDox must be set to appropriate operating levels prior to applying inputs on the I/Os and controls for that port.
- 2. OPTx selects the operating voltage levels for the I/Os and controls on that port. If OPTx is set to VIH (3.3V), then that port's I/Os and controls will operate at 3.3V levels and VDDDX must be supplied at 3.3V. If OPTx is set to VIL (0V), then that port's I/Os and controls will operate at 2.5V levels and VDDDX must be supplied at 2.5V. The OPT pins are independent of one another—both ports can operate at 3.3V levels, both can operate at 2.5V levels, or either can operate at 3.3V with the other at 2.5V.

Truth Table I—Read/Write and Enable Control^(1,2,3)

ŌĒ	CLK	Ē€	CE1	ŪB	ΓB	R/W	Upper Byte I/O9-18	Lower Byte I/O ₀₋₈	MODE		
Х	↑	L	Н	Н	Н	Х	High-Z	High-Z	All Bytes Deselected		
Х	\uparrow	L	Н	Н	L	L	High-Z	Din	Write to Lower Byte Only		
Х	\uparrow	L	Н	L	Н	L	Din	High-Z	Write to Upper Byte Only		
Х	\uparrow	L	Н	L	L	L	Din	Din	Write to Both Bytes		
L	\uparrow	L	Н	Н	L	Н	High-Z	Dout	Read Lower Byte Only		
L	\uparrow	L	Н	L	Н	Н	Dout	High-Z	Read Upper Byte Only		
L	\uparrow	L	Н	L	L	Н	Dout	Dout	Read Both Bytes		
Н	↑	L	Н	L	L	Х	High-Z	High-Z	Outputs Disabled		
NOTES	-			-	-	-	-		- 4832 tbl 02		

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. \overline{ADS} , \overline{CNTEN} , $\overline{CNTRST} = X$.

3. OE is an asynchronous input signal.

70V3389S High-Speed 64K x 18 3.3V Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

4832 tbl 03

Truth Table II—Address Counter Control^(1,2)

Address	Previous Address	Addr Used	CLK	ADS	CNTEN	CNTRST	I/O ⁽³⁾	MODE
Х	Х	0	\uparrow	Х	Х	L ⁽⁴⁾	Dvo(0)	Counter Reset to Address 0
An	Х	An	\uparrow	L ⁽⁴⁾	Х	Н	Dvo (n)	External Address Used
An	Ар	Ар	\uparrow	Н	Н	Н	Dvo(p)	External Address Blocked—Counter disabled (Ap reused)
Х	Ар	Ap + 1	\uparrow	Н	L ⁽⁵⁾	Н	Dvo(p+1)	Counter Enabled—Internal Address generation

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. Read and write operations are controlled by the appropriate setting of R/W, CEo, CE1, BEn and OE.

3. Outputs are in Pipelined mode: the data out will be delayed by one cycle.

4. ADS and CNTRST are independent of all other memory control signals including CEo, CE1 and BEn

5. The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other memory control signals including CE0, CE1, BEn.

Recommended Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature	GND	Vdd
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 150mV
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 150mV
			4832 tbl 04

NOTES:

1. Industrial temperature: for specific speeds, packages and powers contact your sales office.

Recommended DC Operating Conditions with VDDO at 2.5V

Parameter	Min.	Тур.	Max.	Unit
Core Supply Voltage	3.15	3.3	3.45	V
I/O Supply Voltage ⁽³⁾	2.375	2.5	2.625	V
Ground	0	0	0	V
Input High Voltage ⁽³⁾ (Address & Control Inputs)	1.7		Vddq + 125mV ⁽²⁾	V
Input High Voltage - I/O ⁽³⁾	1.7		VDDQ + 125mV ⁽²⁾	V
Input Low Voltage	-0.3(1)		0.7	V
	Core Supply Voltage VO Supply Voltage ⁽³⁾ Ground Input High Voltage ⁽³⁾ (Address & Control Inputs) Input High Voltage - VO ⁽³⁾	Core Supply Voltage3.15VO Supply Voltage ⁽³⁾ 2.375Ground0Input High Voltage ⁽³⁾ (Address & Control Inputs)1.7Input High Voltage - VO ⁽³⁾ 1.7	Core Supply Voltage 3.15 3.3 VO Supply Voltage ⁽³⁾ 2.375 2.5 Ground 0 0 Input High Voltage ⁽³⁾ (Address & Control Inputs) 1.7 — Input High Voltage - VO ⁽³⁾ 1.7 —	Core Supply Voltage 3.15 3.3 3.45 VO Supply Voltage ⁽³⁾ 2.375 2.5 2.625 Ground 0 0 0 Input High Voltage ⁽³⁾ (Address & Control Inputs) 1.7 VDDQ + 125mV ⁽²⁾ Input High Voltage - VO ⁽³⁾ 1.7 VDDQ + 125mV ⁽²⁾

NOTES:

- 1. VIL \geq -1.5V for pulse width less than 10 ns.
- 2. VTERM must not exceed VDDQ + 125mV.
- 3. To select operation at 2.5V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VIL (0V), and VDDOX for that port must be supplied as indicated above.

Absolute Maximum Ratings ⁽¹⁾									
Symbol	Rating	Commercial & Industrial	Unit						
Vterm ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V						
Tbias	Temperature Under Bias	-55 to +125	٥C						
Tstg	Storage Temperature	-65 to +150	٥C						
Іоит	DC Output Current	50	mA						

NOTES:

 Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

2. VTERM must not exceed VDD + 150mV for more than 25% of the cycle time or 4ns maximum, and is limited to \leq 20mA for the period of VTERM \geq VDD + 150mV.

Recommended DC Operating Conditions with VDDQ at 3.3V

Sumbol	Parameter	Min	Turn	Mov	Unit			
Symbol	raiameter	Min.	Тур.	Max.	Unit			
Vdd	Core Supply Voltage	3.15	3.3	3.45	۷			
VDDQ	I/O Supply Voltage ⁽³⁾	3.15	3.3	3.45	V			
Vss	Ground	0	0	0	۷			
Vih	Input High Voltage (Address & Control Inputs) ⁽³⁾	2.0		Vddq + 150mV ⁽²⁾	V			
Vih	Input High Voltage - I/O ⁽³⁾	2.0	-	$V_{DDQ} + 150 mV^{(2)}$	V			
VIL	Input Low Voltage	-0.3 ⁽¹⁾	_	0.8	V			
	4832 tbl 05b							

- 1. VIL \geq -1.5V for pulse width less than 10 ns.
- 2. VTERM must not exceed VDDQ + 150mV.

To select operation at 3.3V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VIH (3.3V), and VDDOX for that port must be supplied as indicated above.

70V3389S High-Speed 64K x 18 3.3V Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

Capacitance⁽¹⁾

(TA = +2)	5°C, F =	= 1.0MHz)	TQFP	ONLY
-----------	----------	-----------	------	------

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit			
Cin	Input Capacitance	VIN = 3dV	8	pF			
Cout ⁽³⁾	Output Capacitance	Vout = 3dV	10.5	pF			
NOTEO							

NOTES:

1. These parameters are determined by device characterization, but are not production tested.

2. 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.

3. COUT also references CI/O.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (VDD = 3.3V ± 150mV)

			70V3	70V3389S	
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
lu	Input Leakage Current ⁽¹⁾	VDDQ = Max., V IN = 0 V to V DDQ		10	μA
llo	Output Leakage Current	\overline{CE}_0 = Vih or CE1 = Vil, Vout = 0V to VDDQ	_	10	μA
Vol (3.3V)	Output Low Voltage ⁽²⁾	IOL = +4mA, VDDQ = Min.	—	0.4	V
Vон (3.3V)	Output High Voltage ⁽²⁾	Ioh = -4mA, VDDQ = Min.	2.4	_	V
Vol (2.5V)	Output Low Voltage ⁽²⁾	IOL = +2mA, $VDDQ = Min$.	—	0.4	V
Voн (2.5V)	Output High Voltage ⁽²⁾	IOH = -2mA, VDDQ = Min.	2.0		V
				4	1832 tbl 08

NOTES:

1. At VDD \leq - 2.0V input leakages are undefined.

2. VDDQ is selectable (3.3V/2.5V) via OPT pins. Refer to p.4 for details.

70V3389S High-Speed 64K x 18 3.3V Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽³⁾ ($V_{DD} = 3.3V \pm 150 \text{mV}$)

						389S4 Only	Co	389S5 m'l Ind		389S6 I Only	
Symbol	Parameter	Test Condition	Versio	on	Тур. ⁽⁴⁾	Мах.	Тур. ⁽⁴⁾	Мах.	Тур. ⁽⁴⁾	Max.	Uni
IDD	Dynamic Operating Current (Both Ports Active)	$\label{eq:cell} \overline{CE}L \text{ and } \overline{CE}R= VIL, \\ Outputs Disabled, \\ f = fMAX^{(1)}$	COM'L	S	375	460	285	360	245	310	m/
			IND	S			285	415	245	360	
ISB1	Standby Current (Both Ports - TTL Level Inputs)	$\overline{CE}L = \overline{CE}R = VIH$ f = fMAX ⁽¹⁾	COM'L	S	145	190	105	145	95	125	m
			IND	S			105	175	95	150	
ISB2	Standby Current (One Port - TTL Level Inputs)	$\overline{CE}^{"A"} = VIL \text{ and } \overline{CE}^{"B"} = VIH^{(5)}$ Active Port Outputs Disabled, f=fMAX ⁽¹⁾	COM'L	S	265	325	190	260	175	225	m
			IND	S			190	300	175	260	
ISB3	Full Standby Current (Both Ports - CMOS Level Inputs)	$\begin{array}{l} \hline Both \ {\sf Ports} \ \overline{\sf CE}{\sf L} \ and \\ \hline \overline{\sf CE}{\sf R} \ \geq \ {\sf VDDQ} \ \cdot \ 0.2{\sf V}, \\ \hline {\sf VIN} \ \geq \ {\sf VDDQ} \ \cdot \ 0.2{\sf V} \ or \ {\sf VIN} \ \leq \ 0.2{\sf V}, \\ f \ = \ 0^{(2)} \end{array}$	COM'L	S	6	15	6	15	6	15	m
			IND	S			6	30	6	30	
ISB4	Full Standby Current (One Port - CMOS Level Inputs)		COM'L	S	265	325	180	260	170	225	m
			IND	S	_		180	300	170	260	

NOTES:

1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS" at input levels of GND to 3V.

2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.

3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

4. VDD = 3.3V, TA = 25°C for Typ, and are not production tested. IDD DC(f=0) = 120mA (Typ).

5. $\overline{CEx} = VIL$ means $\overline{CEox} = VIL$ and CE1x = VIH $\overline{CEx} = VIH$ means $\overline{CEox} = VIH$ or CE1x = VIH

 $\overline{\text{CE}}x \leq 0.2V$ means $\overline{\text{CE}}\textsc{oss} \leq 0.2V$ and $\text{CE}\textsc{iss} \geq V\textsc{dd}$ - 0.2V

 $\overline{CE}x \ge V$ DDQ - 0.2V means \overline{CE} OX $\ge V$ DDQ - 0.2V or CE1X - 0.2V

"X" represents "L" for left port or "R" for right port.

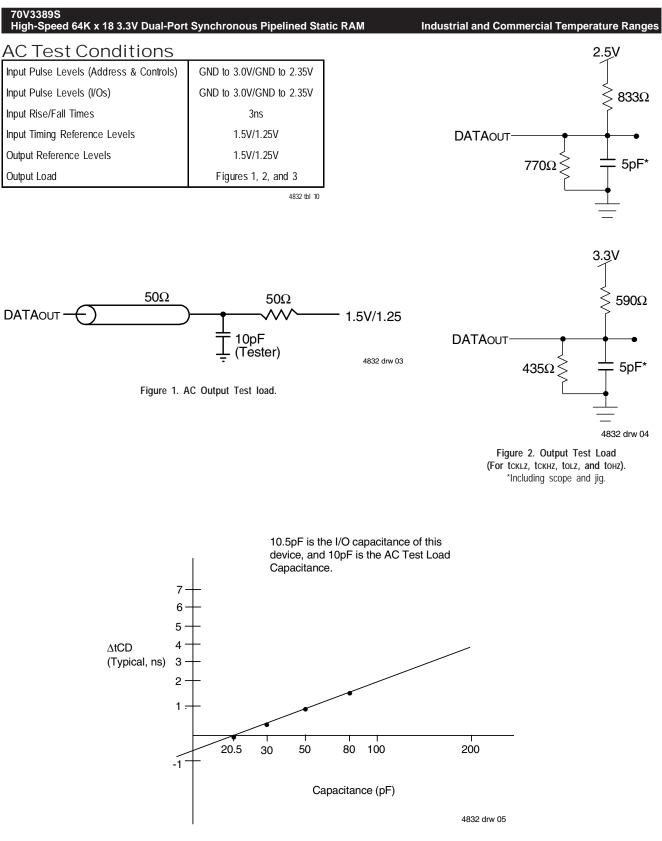


Figure 3. Typical Output Derating (Lumped Capacitive Load).

70V3389S High-Speed 64K x 18 3.3V Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing)^(1,2) (VDD = $3.3V \pm 150$ mV, TA = 0°C to +70°C)

		70V3389S4 Com'l Only		70V3389S5 Com'l & Ind		70V3389S6 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
tcyc2	Clock Cycle Time (Pipelined)	7.5	—	10		12		ns
tCH2	Clock High Time (Pipelined)	3	—	4		5		ns
tCL2	Clock Low Time (Pipelined)	3		4		5		ns
tr	Clock Rise Time		3		3	—	3	ns
tr	Clock Fall Time	—	3		3	—	3	ns
tsa	Address Setup Time	1.8	—	2.0		2.0		ns
tha	Address Hold Time	0.7	—	0.7		1.0		ns
tsc	Chip Enable Setup Time	1.8	—	2.0		2.0		ns
tнc	Chip Enable Hold Time	0.7	_	0.7		1.0		ns
tsв	Byte Enable Setup Time	1.8	_	2.0		2.0		ns
tHB	Byte Enable Hold Time	0.7	_	0.7		1.0		ns
tsw	R/W Setup Time	1.8	_	2.0	_	2.0		ns
tHW	R/\overline{W} Hold Time	0.7	_	0.7		1.0		ns
tsp	Input Data Setup Time	1.8	_	2.0		2.0		ns
thd	Input Data Hold Time	0.7	_	0.7	_	1.0		ns
tsad	ADS Setup Time	1.8	_	2.0		2.0		ns
thad	ADS Hold Time	0.7		0.7		1.0		ns
tscn	CNTEN Setup Time	1.8		2.0		2.0		ns
then	CNTEN Hold Time	0.7	_	0.7		1.0		ns
t SRST	CNTRST Setup Time	1.8	—	2.0		2.0		ns
thrst	CNTRST Hold Time	0.7	_	0.7		1.0		ns
tOE ⁽¹⁾	Output Enable to Data Valid		4		5	_	6	ns
tolz	Output Enable to Output Low-Z	0		0		0		ns
tонz	Output Enable to Output High-Z	1	4	1	4.5	1	5	ns
tCD2	Clock to Data Valid (Pipelined)		4.2		5		6	ns
tDC	Data Output Hold After Clock High	1		1		1		ns
tскнz	Clock High to Output High-Z	1	3	1	4.5	1.5	6	ns
tcklz.	Clock High to Output Low-Z	1	—	1		1		ns
Port-to-Port [Delay	•	•	•	•	•	•	
tco	Clock-to-Clock Offset	6		8		10		ns

NOTES:

1. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE).

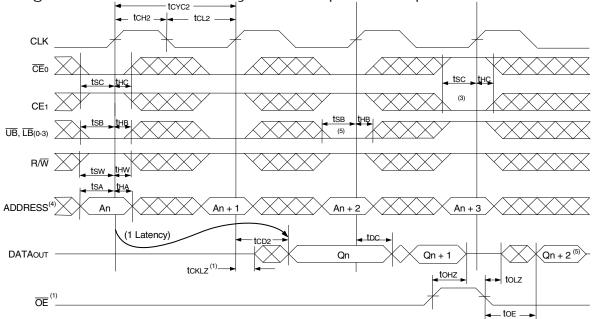
2. These values are valid for either level of VDD0 (3.3V/2.5V). See page 4 for details on selecting the desired I/O voltage levels for each port.

70V3389S High-Speed 64K x 18 3.3V Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

4832 drw 06

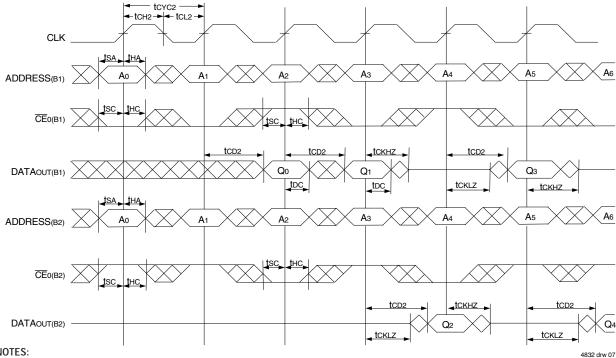
Timing Waveform of Read Cycle for Pipelined Operation⁽²⁾



NOTES:

- 1. OE is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 2. $\overline{ADS} = VIL$, \overline{CNTEN} and $\overline{CNTRST} = VIH$.
- 3. The output is disabled (High-Impedance state) by $\overline{CE}_0 = V_{H}$, $CE_1 = V_{IL}$, \overline{UB} , $\overline{LB} = V_{H}$ following the next rising edge of the clock. Refer to Truth Table 1.
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. If UB or LB was HIGH, then the appropriate Byte of DATAOUT for Qn + 2 would be disabled (High-Impedance state).

Timing Waveform of a Multi-Device Pipelined Read^(1,2)



NOTES:

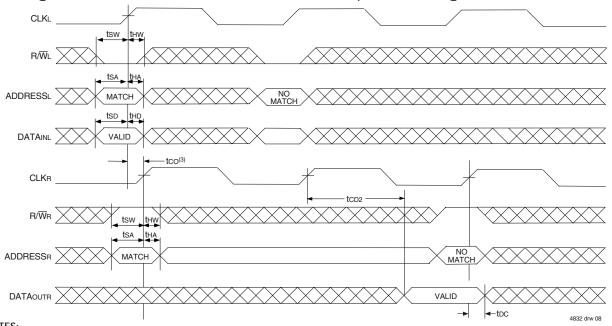
B1 Represents Device #1; B2 Represents Device #2. Each Device consists of one IDT70V3389 for this waveform, 1.

- and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. \overline{UB} , \overline{LB} , \overline{OE} , and \overline{ADS} = VIL; CE1(B1), CE1(B2), R/W, CNTEN, and \overline{CNTRST} = VIH.

70V3389S High-Speed 64K x 18 3.3V Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

Timing Waveform of Left Port Write to Pipelined Right Port Read^(1,2)

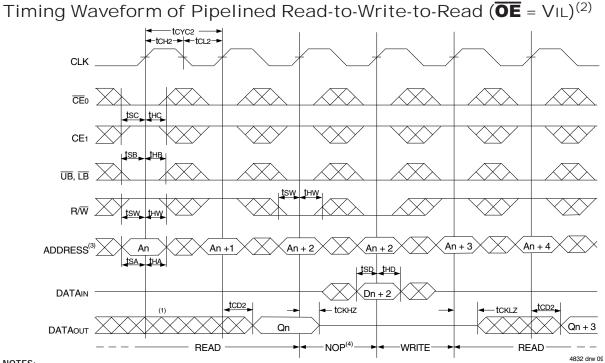


NOTES:

1. \overline{CE}_0 , \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; CE1, \overline{CNTEN} , and \overline{CNTRST} = VIH.

2. \overline{OE} = VIL for the Right Port, which is being read from. \overline{OE} = VIH for the Left Port, which is being written to.

 If tco ≤ minimum specified, then data from right port read is not valid until following right port clock cycle (ie, time from write to valid read on opposite port will be tco + 2 tcyc2 + tcp2). If tco > minimum, then data from right port read is available on first right port clock cycle (ie, time from write to valid read on opposite port will be tco + tcyc + tcp2).



NOTES:

1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.

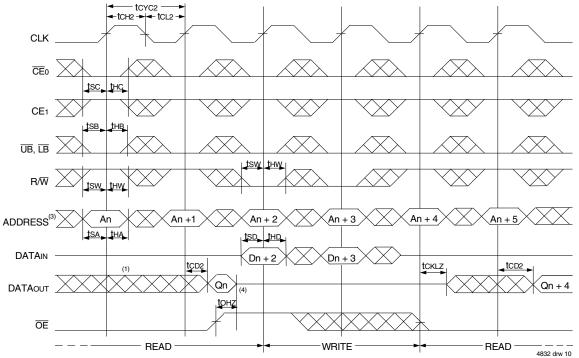
2. CEo, UB, LB, and ADS = VIL; CE1, CNTEN, and CNTRST = VIH. "NOP" is "No Operation".

- 3. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be rewritten to guarantee data integrity.

12

70V3389S High-Speed 64K x 18 3.3V Dual-Port Synchronous Pipelined Static RAM

Timing Waveform of Pipelined Read-to-Write-to-Read (**OE** Controlled)⁽²⁾

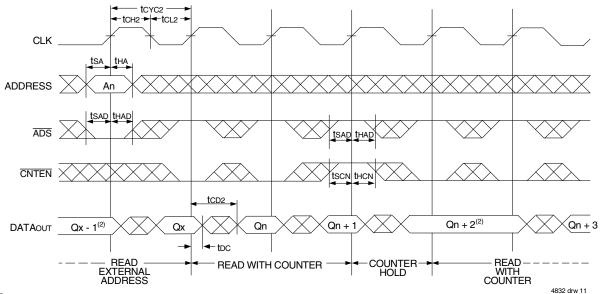


NOTES:

1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.

- 2. CEo, UB, LB, and ADS = VIL; CE1, CNTEN, and CNTRST = VIH.
- 3. Addresses do not have to be accessed sequentially since $\overline{ADS} = VIL$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 4. This timing does not meet requirements for fastest speed grade. This waveform indicates how logically it could be done if timing so allows.

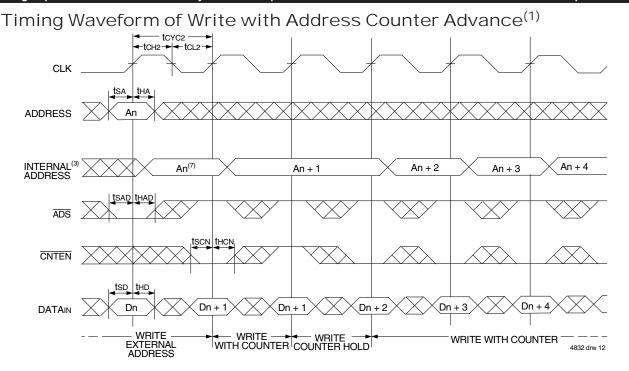
Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾



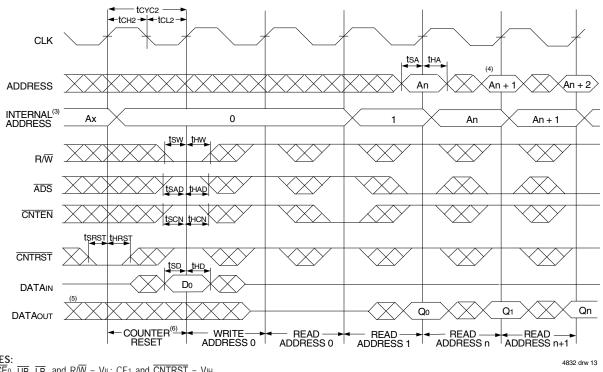
- 1. \overline{CE}_{0} , \overline{OE} , \overline{UB} , \overline{LB} = VIL; CE1, R/W, and \overline{CNTRST} = VIH.
- 2. If there is no address change via \overline{ADS} = VIL (loading a new address) or \overline{CNTEN} = VIL (advancing the address), i.e. \overline{ADS} = VIH and \overline{CNTEN} = VIH, then the data output remains constant for subsequent clocks.

70V3389S High-Speed 64K x 18 3.3V Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges



Timing Waveform of Counter Reset⁽²⁾



- 1. \overline{CE}_{0} , \overline{UB} , \overline{LB} , and $R/\overline{W} = V_{1L}$; CE1 and $\overline{CNTRST} = V_{1H}$.
- 2. \overline{CE}_{0} , \overline{UB} , $\overline{LB} = VIL$; $CE_{1} = VIH$.
- 3. The "Internal Address" is equal to the "External Address" when ADS = VIL and equals the counter output when ADS = VIH.
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset cycle: ADDR 0 will be accessed. Extra cycles are shown here simply for clarification.
- 7. TOTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1'Address is written to during this cycle.

70V3389S High-Speed 64K x 18 3.3V Dual-Port Synchronous Pipelined Static RAM

Functional Description

The IDT70V3389 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the address counters for fast interleaved memory applications.

A HIGH on \overline{CE} or a LOW on CE1 for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70V3389s for depth expansion configurations. Two cycles are required with \overline{CE}_0 LOW and CE1 HIGH to reactivate the outputs.

Depth and Width Expansion

The IDT70V3389 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

The IDT70V3389 can also be used in applications requiring expanded width, as indicated in Figure 4. Through combining the control signals, the devices can be grouped as necessary to accommodate applications needing 36-bits or wider.

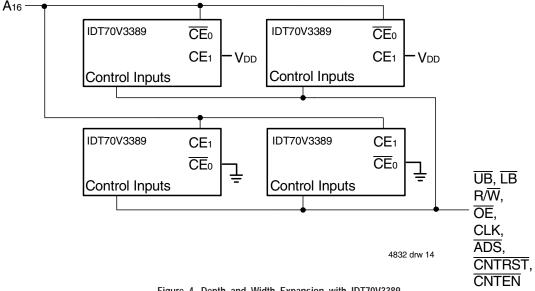
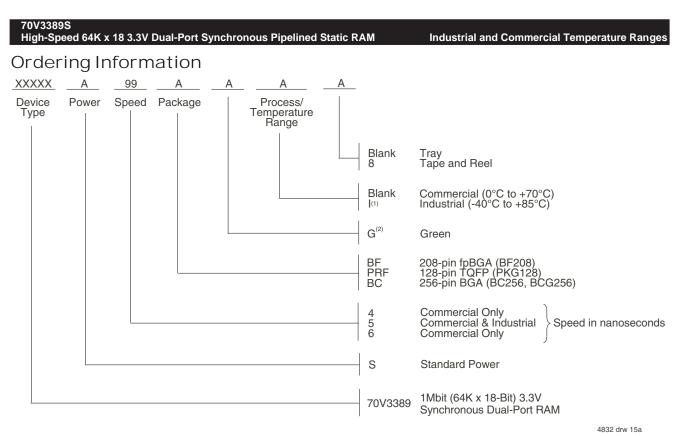


Figure 4. Depth and Width Expansion with IDT70V3389



NOTES:

- 1. Contact your local sales office for Industrial temp range in other speeds, packages and powers.
- 2. Green parts available. For specific speeds, packages and powers contact your local sales office. LEAD FINISH (SnPb) parts are Obsolete. Product Discontinuation Notice - PDN# SP-17-02

Note that information regarding recently obsoleted parts are included in this datasheet for customer convenience.

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
4	70V3389S4BC	BC256	CABGA	С
	70V3389S4BC8	BC256	CABGA	С
	70V3389S4BCG	BCG256	CABGA	С
	70V3389S4BF	BF208	CABGA	С
	70V3389S4BF8	BF208	CABGA	С
	70V3389S4PRFG	PKG128	TQFP	С
	70V3389S4PRFG8	PKG128	TQFP	С
5	70V3389S5BC	BC256	CABGA	С
	70V3389S5BC8	BC256	CABGA	С
	70V3389S5BCI	BC256	CABGA	I
	70V3389S5BCI8	BC256	CABGA	I
	70V3389S5BF	BF208	CABGA	С
	70V3389S5BF8	BF208	CABGA	С
	70V3389S5BFI	BF208	CABGA	I
	70V3389S5BFI8	BF208	CABGA	I
6	70V3389S6BC	BC256	CABGA	С
	70V3389S6BC8	BC256	CABGA	С
	70V3389S6BF	BF208	CABGA	С
	70V3389S6BF8	BF208	CABGA	С

Orderable Part Information

70V3389S High-Speed 64K x 18 3.3V Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

Datasheet Document History

01/18/99:	Initial Public Release
03/15/99:	Page 9 Additional notes
04/28/99:	Added fpBGA package
06/08/99:	Page 2 Changed package body height from 1.5mm to 1.4mm
06/15/99:	Page 5 Deleted note 6 for Table II
0714//99:	Page 2 Corrected pin T3 to VDDQL
08/04/99:	Page 6 Improved power numbers
10/01/99:	Upgraded speed to 133MHz, added 2.5V I/O capability
11/12/99:	Replaced IDT logo
02/28/00:	Added new BGA package, added full 2.5V interface capability
05/01/00:	Page 2 Added ball pitch
	Page 3 Renamed pins
	Page 6 Made corrections to Truth Table
	Page 9 Changed Ω numbers in figure 2
01/10/01:	Page 4 Added information to pin and pin notes
	Page 6 Increased storage temperature parameter
	Clarified TA Parameter
	Page 8 DC Electrical parameters-changed wording from "open" to "disabled"
	Removed note 7 on DC Characteristics table
	Removed Preliminary status
04/10/01:	Added Industrial Temperature Ranges and removed related notes
02/12/01:	Page 2, 3 & 4 Added date revision to pin configurations
	Page 6 Removed industrial temp footnote from table 04
	Page 8 & 10 Removed industrial temp for 6ns from DC & AC Electrical Characteristic
	Page 16 Removed industrial temp from 6ns in ordering information
	Added industrial temp footnote
04/05/04	Page 1 & 17 Replaced TM logo with ® logo
01/05/06:	Page 1 Added green availability to features
00100107	Page 16 Added green indicator to ordering information
02/08/06:	Page 5 Changed footnote 2 for Truth Table I from ADS, CNTEN, CNTRST = VIH to ADS, CNTEN, CNTRST = X
07/25/08:	Page 8 Corrected a typo in the DC Chars table
01/19/09:	Page 16 Removed "IDT" from orderable part number
10/03/14:	Page 16 Added Tape & Reel to Ordering Information
02/15/18:	Product Discontinuation Notice - PDN# SP-17-02
07/10/10	Last time buy expires June 15, 2018
07/19/19:	Page 2, 3 & 4 Updated package codes BF-208 to BF208, BC-256 to BC256, BCG256 and PK-128 to PKG128
	Page 16 Added Orderable Part Information

IMPORTANT NOTICE AND DISCLAIMER

RENESAS ELECTRONICS CORPORATION AND ITS SUBSIDIARIES ("RENESAS") PROVIDES TECHNICAL SPECIFICATIONS AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS OR IMPLIED, INCLUDING, WITHOUT LIMITATION, ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for developers skilled in the art designing with Renesas products. You are solely responsible for (1) selecting the appropriate products for your application, (2) designing, validating, and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. Renesas grants you permission to use these resources only for development of an application that uses Renesas products. Other reproduction or use of these resources is strictly prohibited. No license is granted to any other Renesas intellectual property or to any third party intellectual property. Renesas disclaims responsibility for, and you will fully indemnify Renesas and its representatives against, any claims, damages, costs, losses, or liabilities arising out of your use of these resources. Renesas' products are provided only subject to Renesas' Terms and Conditions of Sale or other applicable terms agreed to in writing. No use o any Renesas resources expands or otherwise alters any applicable warranties or warranty disclaimers for these products.

(Disclaimer Rev.1.0 Mar 2020)

Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu, Koto-ku, Tokyo 135-0061, Japan www.renesas.com

Trademarks

Renesas and the Renesas logo are trademarks of Renesas Electronics Corporation. All trademarks and registered trademarks are the property of their respective owners. **Contact Information**

For further information on a product, technology, the most up-to-date version of a document, or your nearest sales office, please visit: <u>www.renesas.com/contact/</u>